

High-performance Monolayer Na₃Sb Shrinking Transistors: A DFT-NEGF Study

Wenhan Zhou,^a Shengli Zhang,^{*a} Shiyong Guo,^a Hengze Qu,^a Bo Cai,^a Xiang Chen,^a and Haibo Zeng^{*a}

^aKey Laboratory of Advanced Display Materials and Devices, Ministry of Industry and Information Technology, College of Material Science and Engineering, Nanjing University of Science and Technology, Nanjing 210094, P. R. China

*Authors to whom correspondence should be addressed: zhangslvip@njust.edu.cn and zeng.haibo@njust.edu.cn

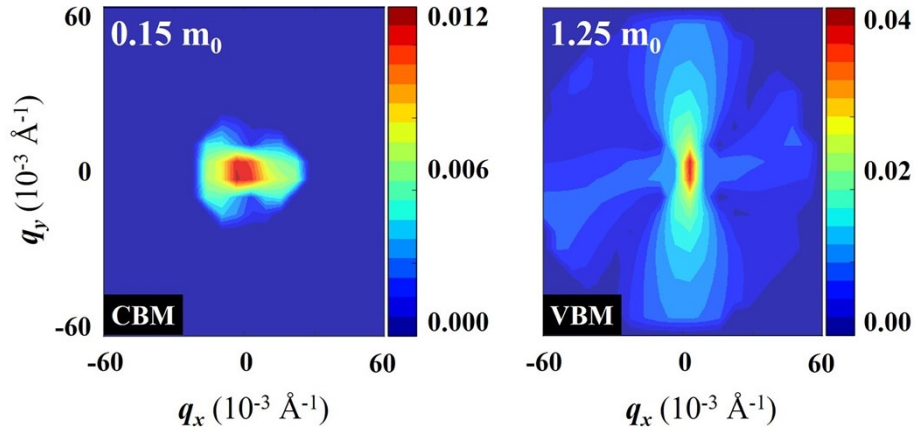


Fig. S1. Matrix elements of electron-phonon interaction in monolayer Na₃Sb. The interaction is illustrated as a function of the phonon wave vector q for k at the CBM and VBM k -points.

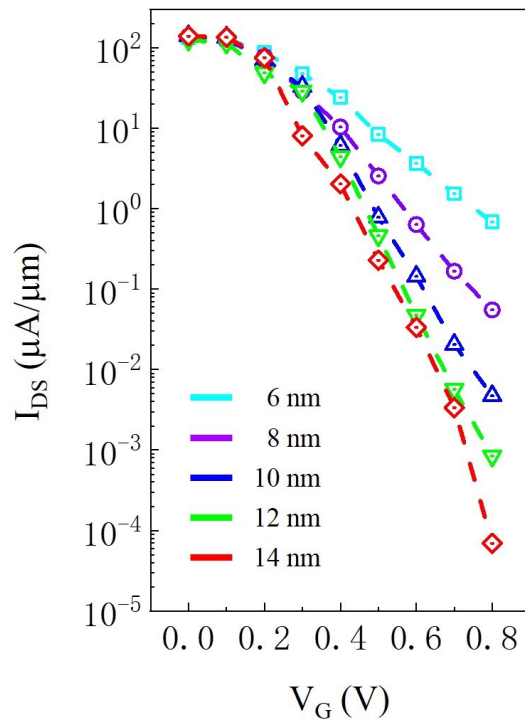


Fig. S2. Transfer characteristics of the p-type Na₃Sb FETs for different channel lengths.

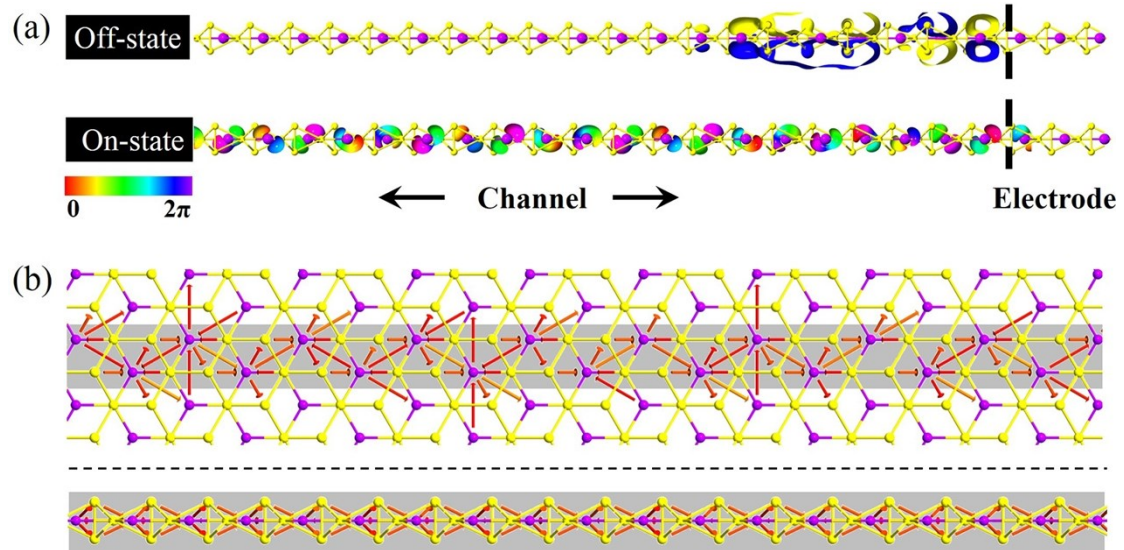


Fig. S3 (a) Transmission eigenstates of the Na_3Sb FETs at the off and on state. (b) Top and side view for transmission pathway of the Na_3Sb FETs at the on state.